

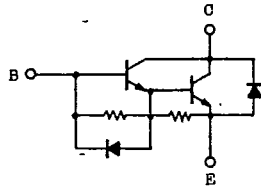
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16279 DT-33-35

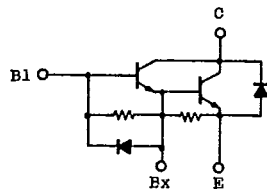


**SEMICONDUCTOR**  
TECHNICAL DATA

MG200H1AL2  
MG200H1FL1A

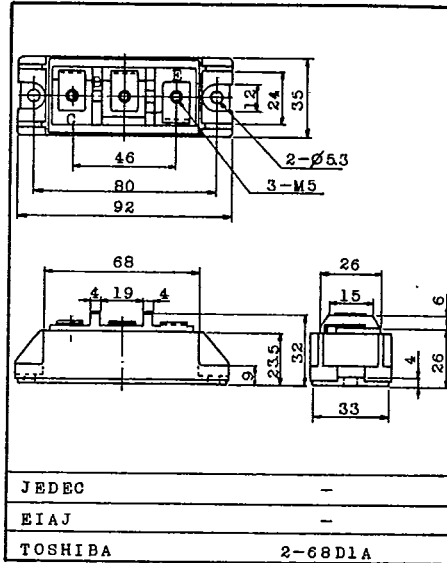


MG200H1AL2



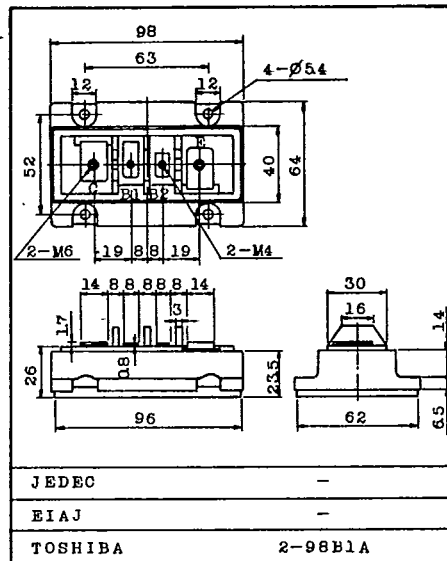
MG200H1FL1

Unit in mm



Weight : 210g

Unit in mm



Weight : 420g

TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16280

DT-33-35



# SEMICONDUCTOR

## TECHNICAL DATA

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## MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB10</sub>	600	V
Collector-Emitter Voltage	V <sub>CEO</sub>	600	V
Collector-Emitter Sustaining Voltage	V <sub>CEO(SUS)</sub>	550	V
Emitter-Base Voltage	V <sub>EB10</sub>	6	V
Collector Current	DC	I <sub>C</sub>	200
	1ms	I <sub>C</sub>	400
	DC	-I <sub>C</sub>	200
Base Current	I <sub>B1</sub>	8	A
Collector Power Dissipation (Tc=25°C)	P <sub>C</sub>	800	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-40~125	°C
Isolation Voltage	V <sub>isol</sub>	2500 (AC 1 Minute)	V
Screw Torque (Terminal M4/M6/Mounting)	-	20/30/30	kg·cm

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I <sub>CB10</sub>	V <sub>CB1</sub> =600V, I <sub>E</sub> =0	-	-	2.0	mA	
Emitter Cut-off Current	I <sub>EB10</sub>	V <sub>EB1</sub> =6V, I <sub>C</sub> =0	-	-	400	mA	
Collector-Emitter Sustaining Voltage	V <sub>CEO(SUS)</sub>	I <sub>C</sub> =0.5A, L=40mH	550	-	-	V	
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =200A	80	-	-		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =200A, I <sub>B1</sub> =6A	-	-	2.0	V	
Base-Emitter Saturation Voltage	V <sub>BE1(sat)</sub>		-	-	2.7	V	
Emitter-Collector Voltage	V <sub>ECO</sub>	I <sub>E</sub> =200A, I <sub>B1</sub> =0	-	-	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	-I <sub>C</sub> =200A, V <sub>EB1</sub> =3V V <sub>CE</sub> =300V	-	-	2.0	μs	
Collector Output Capacitance	C <sub>ob1</sub>	V <sub>CB1</sub> =50V, I <sub>E</sub> =0 f=1MHz	-	1670	-	pF	
Switching Time	Turn-on Time	t <sub>on</sub>			2.0	μs	
	Storage Time	t <sub>stg</sub>			-		12
	Fall Time	t <sub>f</sub>			I <sub>B1</sub> =-I <sub>B2</sub> =6A DUTY CYCLE=0.5%		-
Thermal Resistance (Junction to Case)	R <sub>th(j-c)</sub>	Transistor	-	-	0.156	°C/W	
		Diode	-	-	0.65		

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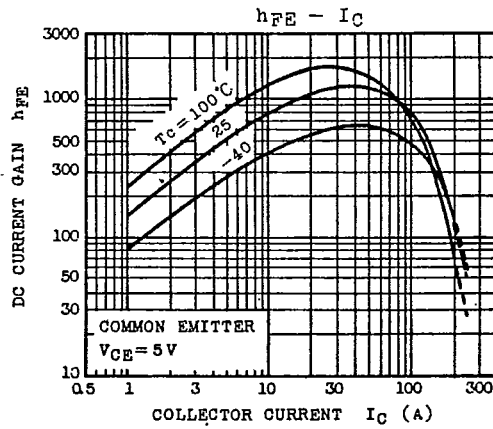
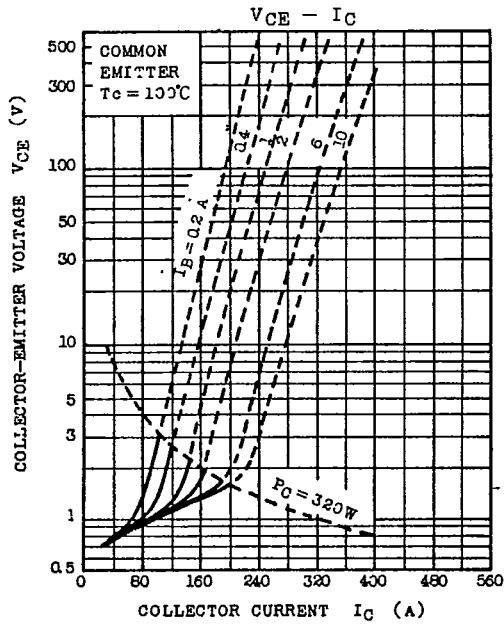
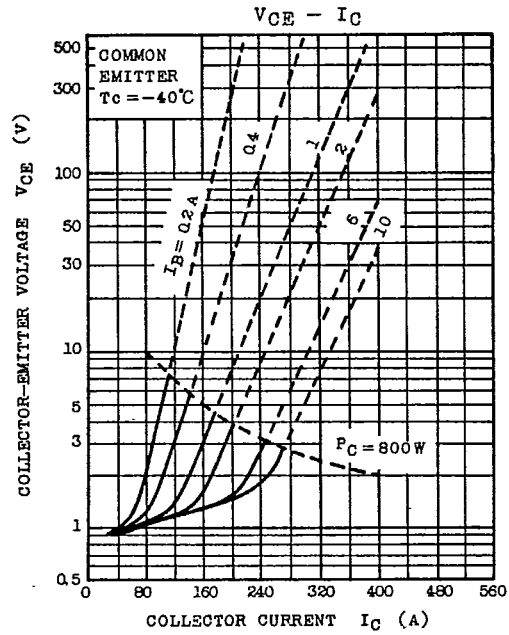
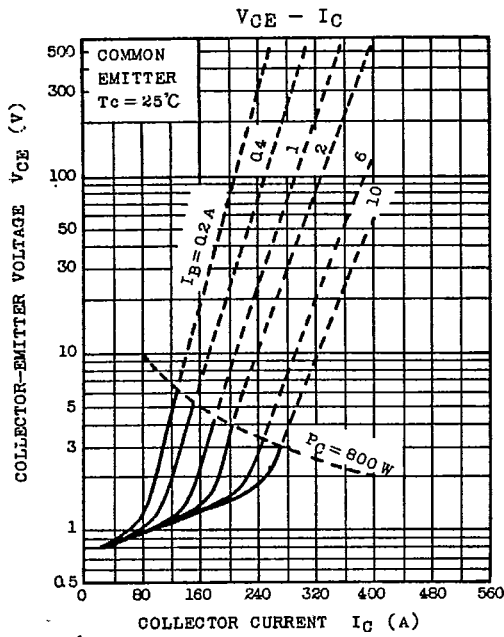
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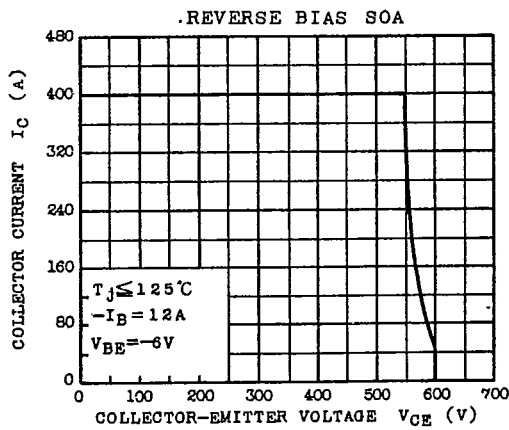
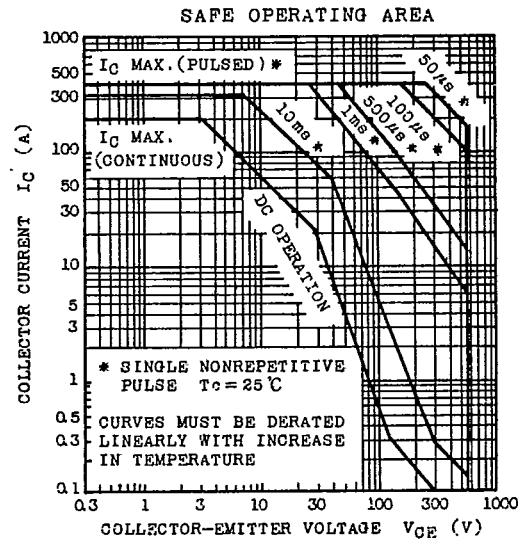
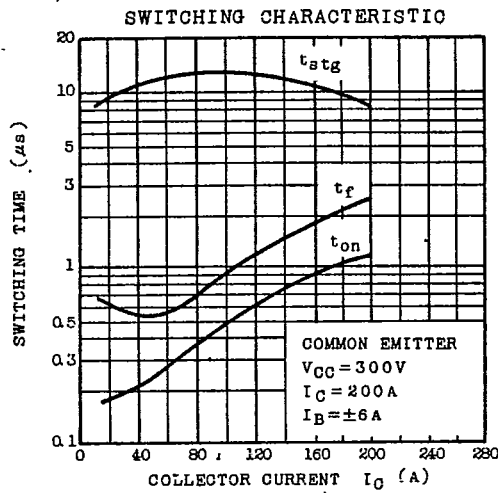
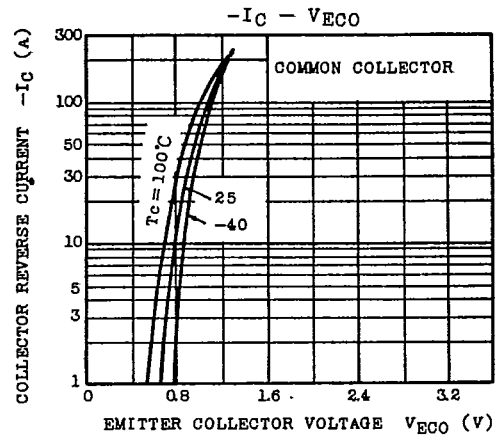
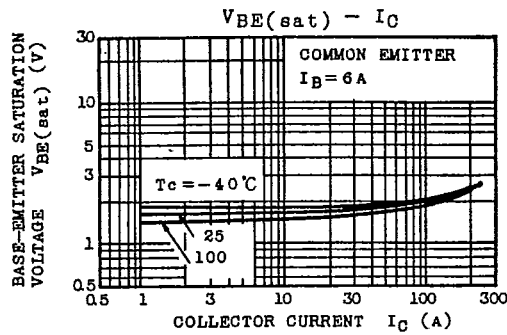
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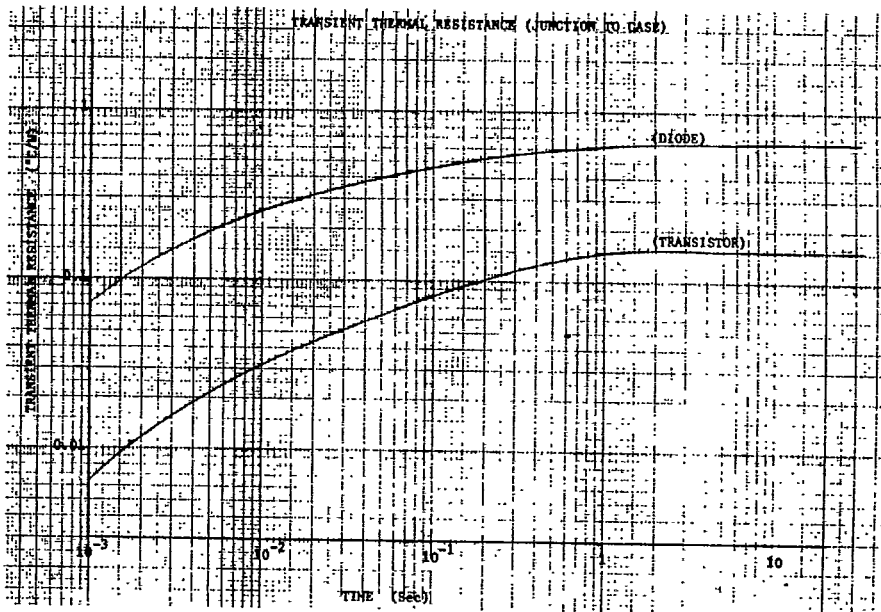
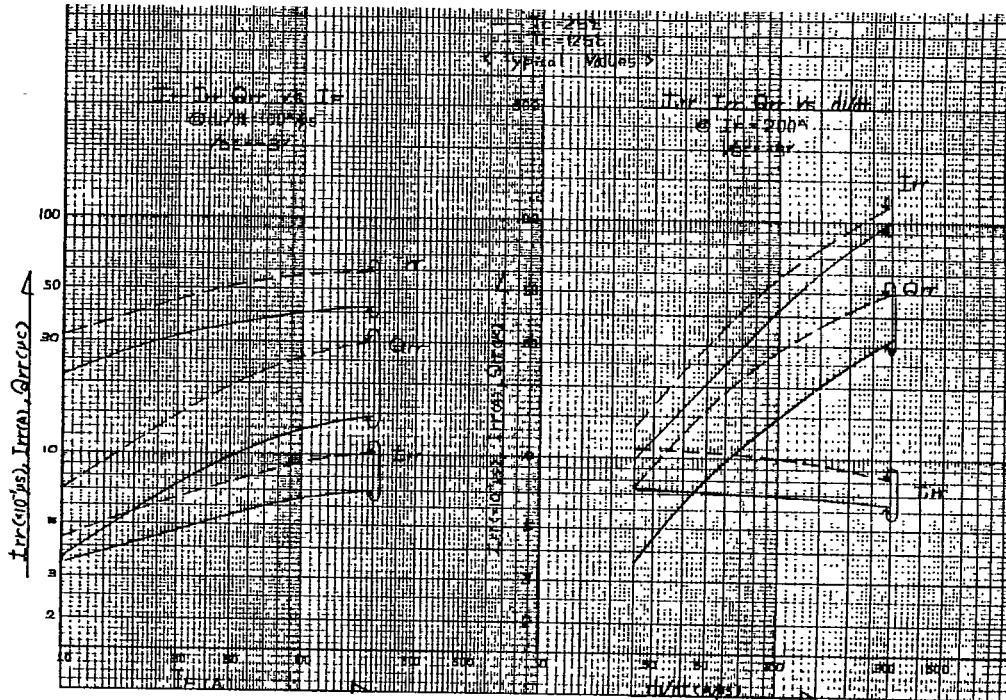


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